

# 74AUP1G86

Low-power 2-input EXCLUSIVE-OR gate

Rev. 02.00 — 16 May 2006

Product data sheet

## 1. General description

The 74AUP1G86 is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74AUP1G86 provides the single 2-input EXCLUSIVE-OR function.

## 2. Features

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
  - ◆ JESD8-12 (0.8 V to 1.3 V)
  - ◆ JESD8-11 (0.9 V to 1.65 V)
  - ◆ JESD8-7 (1.2 V to 1.95 V)
  - ◆ JESD8-5 (1.8 V to 2.7 V)
  - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
  - ◆ HBM JESD22-A114-C Class 3A. Exceeds 5000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
  - ◆ CDM JESD22-C101-C exceeds 1000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu\text{A}$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot  $< 10\%$  of  $V_{CC}$
- $I_{OFF}$  circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

**PHILIPS**

### 3. Ordering information

Table 1: Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74AUP1G86GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1G86GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74LVC1G86GF	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

### 4. Marking

Table 2: Marking

Type number	Marking code
74AUP1G86GW	pH
74AUP1G86GM	pH
74AUP1G86GF	pH

### 5. Functional diagram

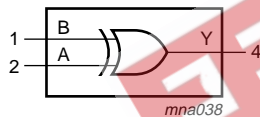


Fig 1. Logic symbol

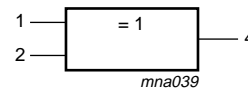


Fig 2. IEC logic symbol

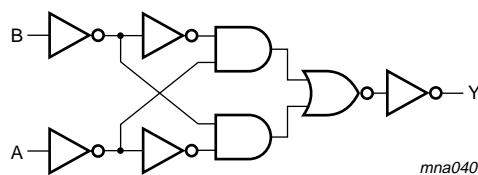


Fig 3. Logic diagram

## 6. Pinning information

### 6.1 Pinning

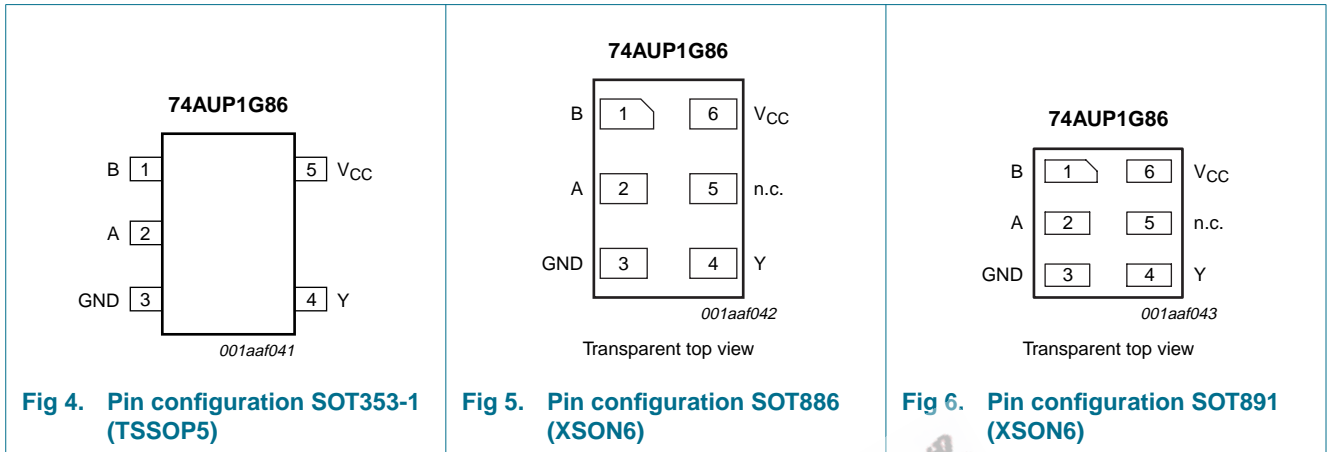


Fig 4. Pin configuration SOT353-1 (TSSOP5)

Fig 5. Pin configuration SOT886 (XSON6)

Fig 6. Pin configuration SOT891 (XSON6)

### 6.2 Pin description

Table 3: Pin description

Symbol	Pin		Description
	TSSOP5	XSON6	
B	1	1	data input B
A	2	2	data input A
GND	3	3	ground (0 V)
Y	4	4	data output Y
n.c.	-	5	not connected
V <sub>CC</sub>	5	6	supply voltage

## 7. Functional description

Table 4: Function table [1]

Input		Output
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	L

[1] H = HIGH voltage level;  
L = LOW voltage level.

## 8. Limiting values

**Table 5: Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+4.6	V
$I_{IK}$	input clamping current	$V_I < 0$ V	-	-50	mA
$V_I$	input voltage		[1] -0.5	+4.6	V
$I_{OK}$	output clamping current	$V_O < 0$ V	-	-50	mA
$V_O$	output voltage	active mode	[1] -0.5	$V_{CC} + 0.5$	V
		Power-down mode	[1] -0.5	+4.6	V
$I_O$	output current	$V_O = 0$ V to $V_{CC}$	-	$\pm 20$	mA
$I_{CC}$	quiescent supply current		-	+50	mA
$I_{GND}$	ground current		-	-50	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP5 packages: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.

For XSON6 packages: above 45 °C the value of  $P_{tot}$  derates linearly with 2.4 mW/K.

## 9. Recommended operating conditions

**Table 6: Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		0.8	3.6	V
$V_I$	input voltage		0	3.6	V
$V_O$	output voltage	active mode	0	$V_{CC}$	V
		Power-down mode; $V_{CC} = 0$ V	0	3.6	V
$T_{amb}$	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8$ V to 3.6 V	0	200	ns/V

## 10. Static characteristics

**Table 7: Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = 25 °C</b>						
V <sub>IH</sub>	HIGH-state input voltage	V <sub>CC</sub> = 0.8 V	0.70 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-state input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.30 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-state output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.75 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.11	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.32	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	2.05	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.72	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.6	-	-	V
V <sub>OL</sub>	LOW-state output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.31	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.44	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.31	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.44	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.1	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.2	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.2	μA
I <sub>CC</sub>	quiescent supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.5	μA
ΔI <sub>CC</sub>	additional quiescent supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	<a href="#">[1]</a>	-	40	μA
C <sub>I</sub>	input capacitance	V <sub>CC</sub> = 0 V to 3.6 V; V <sub>I</sub> = GND or V <sub>CC</sub>	-	0.8	-	pF
C <sub>O</sub>	output capacitance	V <sub>O</sub> = GND; V <sub>CC</sub> = 0 V	-	1.7	-	pF

Table 7: Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>IH</sub>	HIGH-state input voltage	V <sub>CC</sub> = 0.8 V	0.70 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-state input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.30 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-state output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.7 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.03	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.30	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.97	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.85	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.67	-	-	V
V <sub>OL</sub>	LOW-state output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.33	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.33	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.5	μA
		V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.5	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.6	μA
I <sub>CC</sub>	quiescent supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.9	μA
ΔI <sub>CC</sub>	additional quiescent supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	[1]	-	50	μA

**Table 7: Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>IH</sub>	HIGH-state input voltage	V <sub>CC</sub> = 0.8 V	0.75 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.70 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-state input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.25 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.30 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-state output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.11	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.6 × V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	0.93	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.17	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.77	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.67	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.40	-	-	V
V <sub>OL</sub>	LOW-state output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.33 × V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.41	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.39	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.36	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.50	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.75	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V	-	-	±0.75	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC</sub> = 0 V to 0.2 V	-	-	±0.75	μA
I <sub>CC</sub>	quiescent supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 0.8 V to 3.6 V	-	-	1.4	μA
ΔI <sub>CC</sub>	additional quiescent supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 3.3 V	[1]	-	75	μA

[1] One input at V<sub>CC</sub> - 0.6 V, other input at V<sub>CC</sub> or GND.

## 11. Dynamic characteristics

**Table 8: Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#)

Symbol	Parameter	Conditions	Min	Typ <sup>[1]</sup>	Max	Unit
<b><math>T_{amb} = 25\text{ }^{\circ}\text{C}; C_L = 5\text{ pF}</math></b>						
$t_{PHL}, t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>				
		$V_{CC} = 0.8\text{ V}$	-	21.2	-	ns
		$V_{CC} = 1.1\text{ V to }1.3\text{ V}$	2.3	5.9	13.1	ns
		$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	1.8	4.1	7.7	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	1.5	3.3	5.9	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.2	2.6	4.4	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	1.0	2.3	4.0	ns
<b><math>T_{amb} = 25\text{ }^{\circ}\text{C}; C_L = 10\text{ pF}</math></b>						
$t_{PHL}, t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>				
		$V_{CC} = 0.8\text{ V}$	-	24.7	-	ns
		$V_{CC} = 1.1\text{ V to }1.3\text{ V}$	2.6	6.8	14.8	ns
		$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	2.2	4.8	8.7	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	1.8	3.9	6.7	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.5	3.1	5.2	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	1.3	2.9	4.8	ns
<b><math>T_{amb} = 25\text{ }^{\circ}\text{C}; C_L = 15\text{ pF}</math></b>						
$t_{PHL}, t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>				
		$V_{CC} = 0.8\text{ V}$	-	28.2	-	ns
		$V_{CC} = 1.1\text{ V to }1.3\text{ V}$	3.0	7.6	16.5	ns
		$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	2.4	5.3	9.6	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	2.1	4.4	7.5	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.8	3.6	5.9	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	1.6	3.3	5.4	ns
<b><math>T_{amb} = 25\text{ }^{\circ}\text{C}; C_L = 30\text{ pF}</math></b>						
$t_{PHL}, t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>				
		$V_{CC} = 0.8\text{ V}$	-	38.5	-	ns
		$V_{CC} = 1.1\text{ V to }1.3\text{ V}$	3.9	9.9	21.5	ns
		$V_{CC} = 1.4\text{ V to }1.6\text{ V}$	3.2	6.9	12.5	ns
		$V_{CC} = 1.65\text{ V to }1.95\text{ V}$	2.8	5.7	9.8	ns
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	2.4	4.7	7.6	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$	2.2	4.4	7.1	ns



**Table 8: Dynamic characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#)

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
<b>T<sub>amb</sub> = 25 °C</b>						
C <sub>PD</sub>	power dissipation capacitance	f = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub>	[2]			
		V <sub>CC</sub> = 0.8 V	-	2.7	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	2.9	-	pF
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	3.0	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	3.1	-	pF
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	3.6	-	pF
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	4.2	-	pF

- [1] All typical values are measured at nominal V<sub>CC</sub>.
- [2] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 f<sub>i</sub> = input frequency in MHz;  
 f<sub>o</sub> = output frequency in MHz;  
 C<sub>L</sub> = output load capacitance in pF;  
 V<sub>CC</sub> = supply voltage in V;  
 N = number of inputs switching;  
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

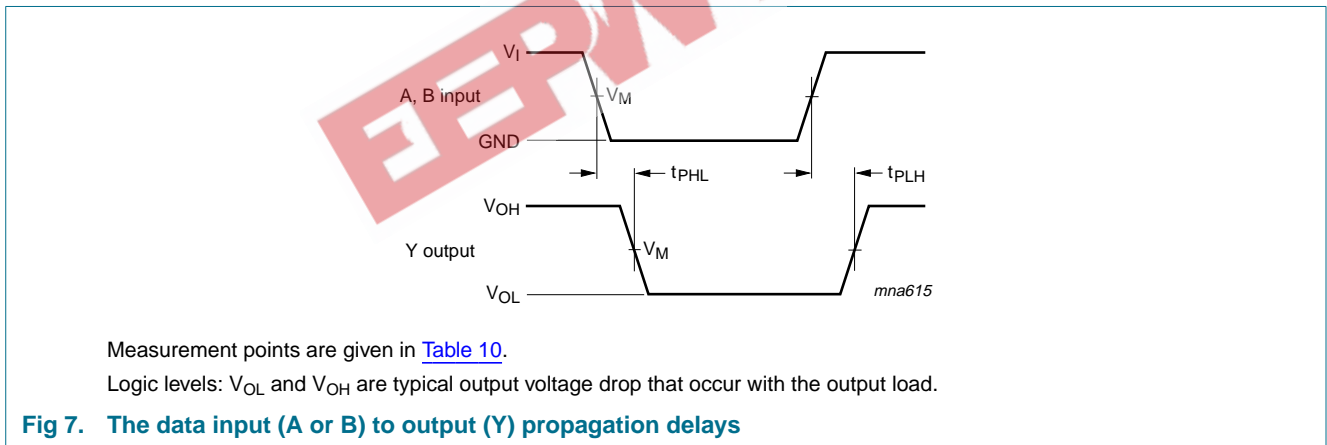
**Table 9: Dynamic characteristics**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#)

Symbol	Parameter	Conditions	-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Max	Min	Max	
<b>C<sub>L</sub> = 5 pF</b>							
t <sub>PHL</sub> , t <sub>PLH</sub>	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>					
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.1	14.3	2.1	15.8	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	1.6	8.8	1.6	9.7	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.4	6.9	1.4	7.6	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.1	5.3	1.1	5.9	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.9	4.7	0.9	5.2	ns
<b>C<sub>L</sub> = 10 pF</b>							
t <sub>PHL</sub> , t <sub>PLH</sub>	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>					
		V <sub>CC</sub> = 1.1 V to 1.3 V	2.4	16.2	2.4	17.9	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	1.9	10.0	1.9	11.0	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.7	8.0	1.7	8.8	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.4	6.2	1.4	6.9	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.3	5.6	1.3	6.2	ns

**Table 9: Dynamic characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 8](#)

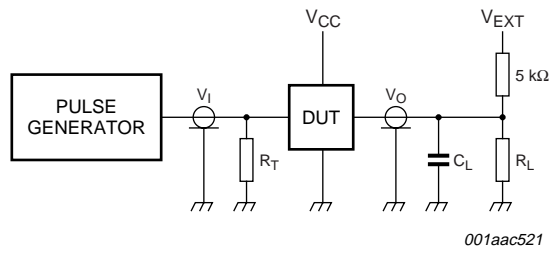
Symbol	Parameter	Conditions	-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Max	Min	Max	
<b><math>C_L = 15 \text{ pF}</math></b>							
$t_{PHL}, t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.7	18.1	2.7	20.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.2	11.3	2.2	12.5	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.9	9.0	1.9	9.9	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	7.0	1.6	7.7	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.5	6.4	1.5	7.1	ns
<b><math>C_L = 30 \text{ pF}</math></b>							
$t_{PHL}, t_{PLH}$	HIGH-to-LOW and LOW-to-HIGH propagation delay A or B to Y	see <a href="#">Figure 7</a>					
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.5	24.1	3.5	26.6	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	2.8	14.8	2.8	16.3	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	2.5	11.7	2.5	12.9	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	2.2	9.1	2.2	10.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.1	8.3	2.1	9.2	ns

12. Waveforms



**Table 10: Measurement points**

Supply voltage	Output	Input		
$V_{CC}$	$V_M$	$V_M$	$V_I$	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{CC}$	$\leq 3.0 \text{ ns}$



Test data is given in [Table 11](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

**Fig 8. Load circuitry for switching times**

**Table 11: Test data**

Supply voltage	Load		$V_{EXT}$		
$V_{CC}$	$C_L$	$R_L$ [1]	$t_{PLH}, t_{PHL}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times  $R_L = 5 \text{ k}\Omega$ , for measuring propagation delays, setup and hold times and pulse width  $R_L = 1 \text{ M}\Omega$ .

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

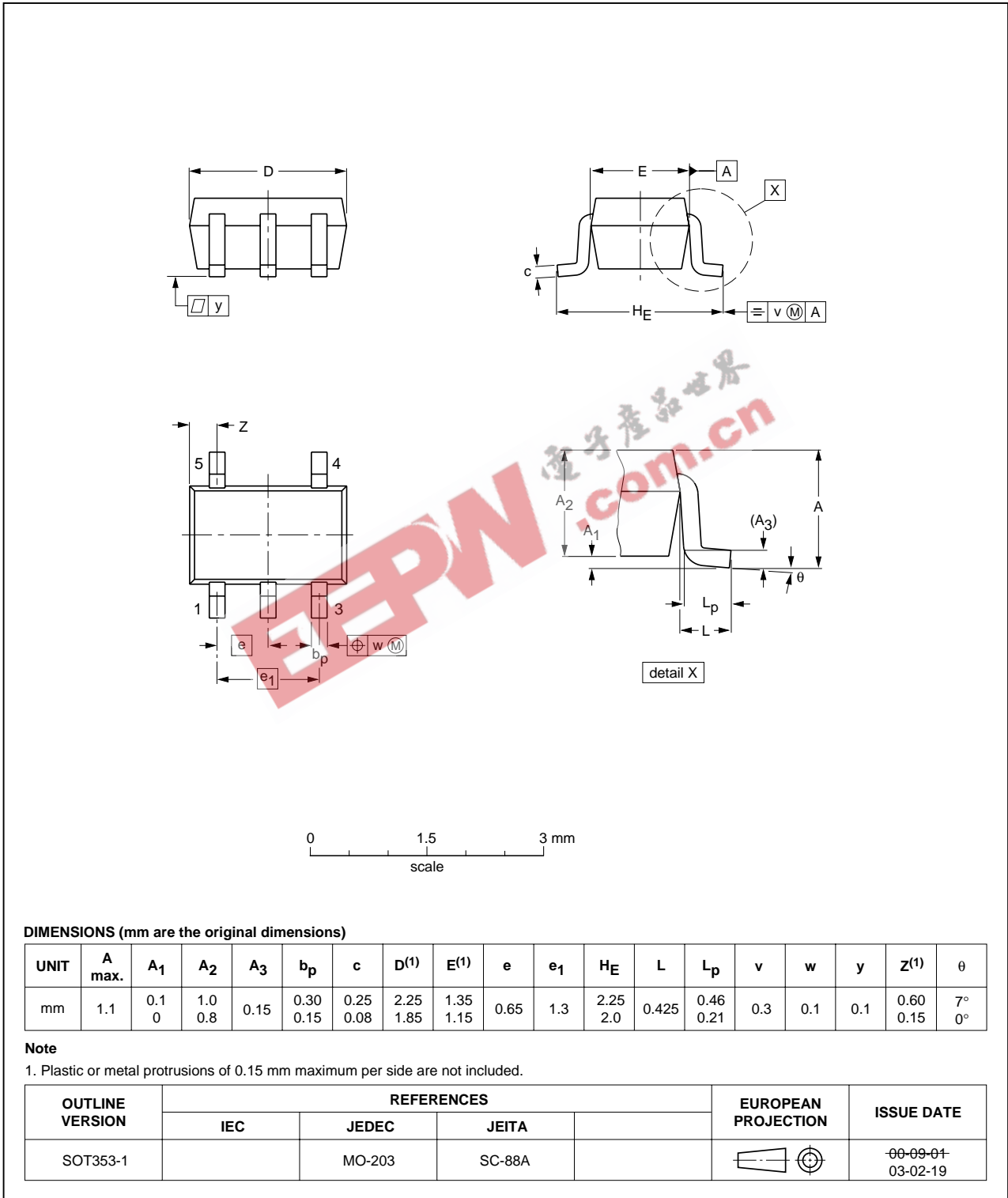


Fig 9. Package outline SOT353-1 (TSSOP5)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

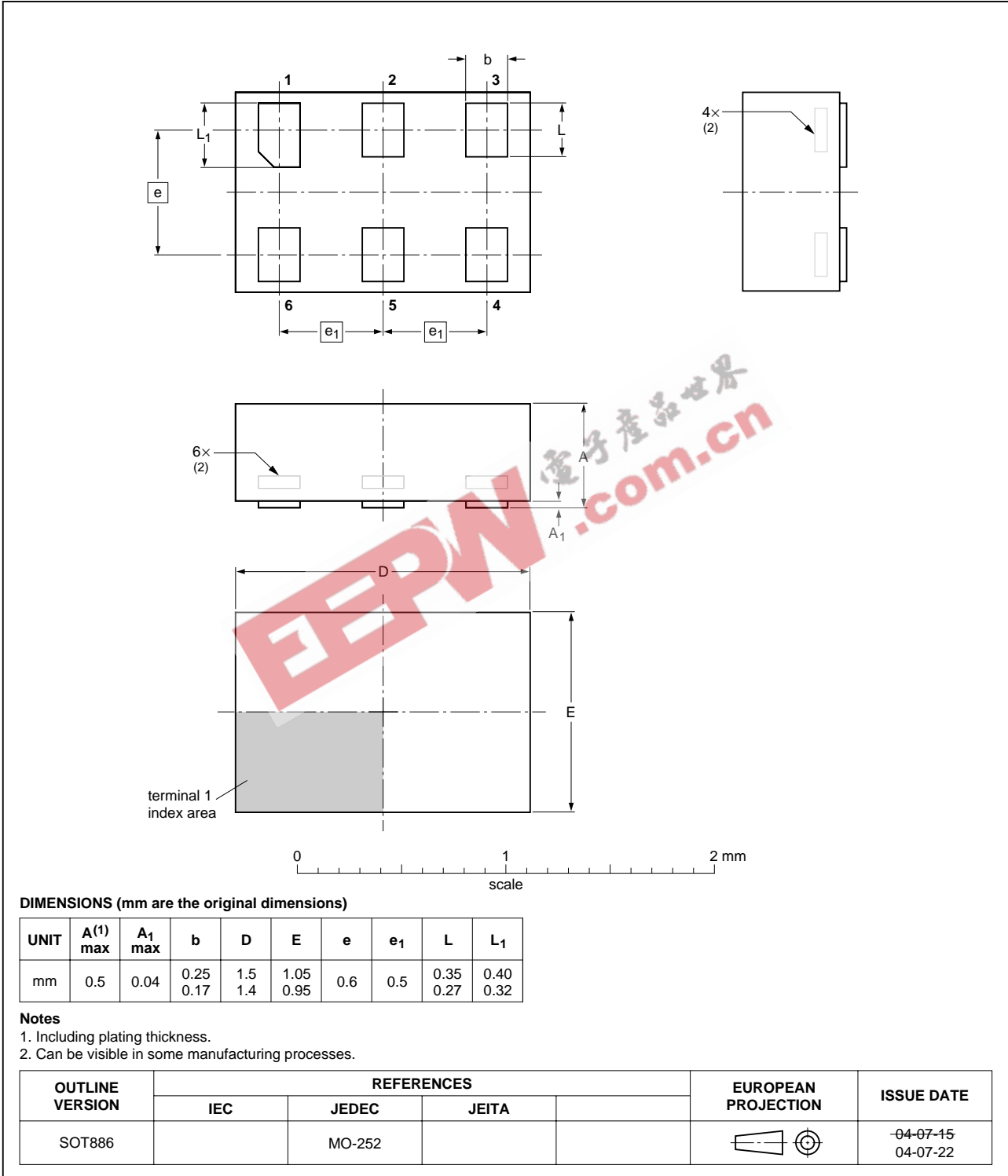


Fig 10. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

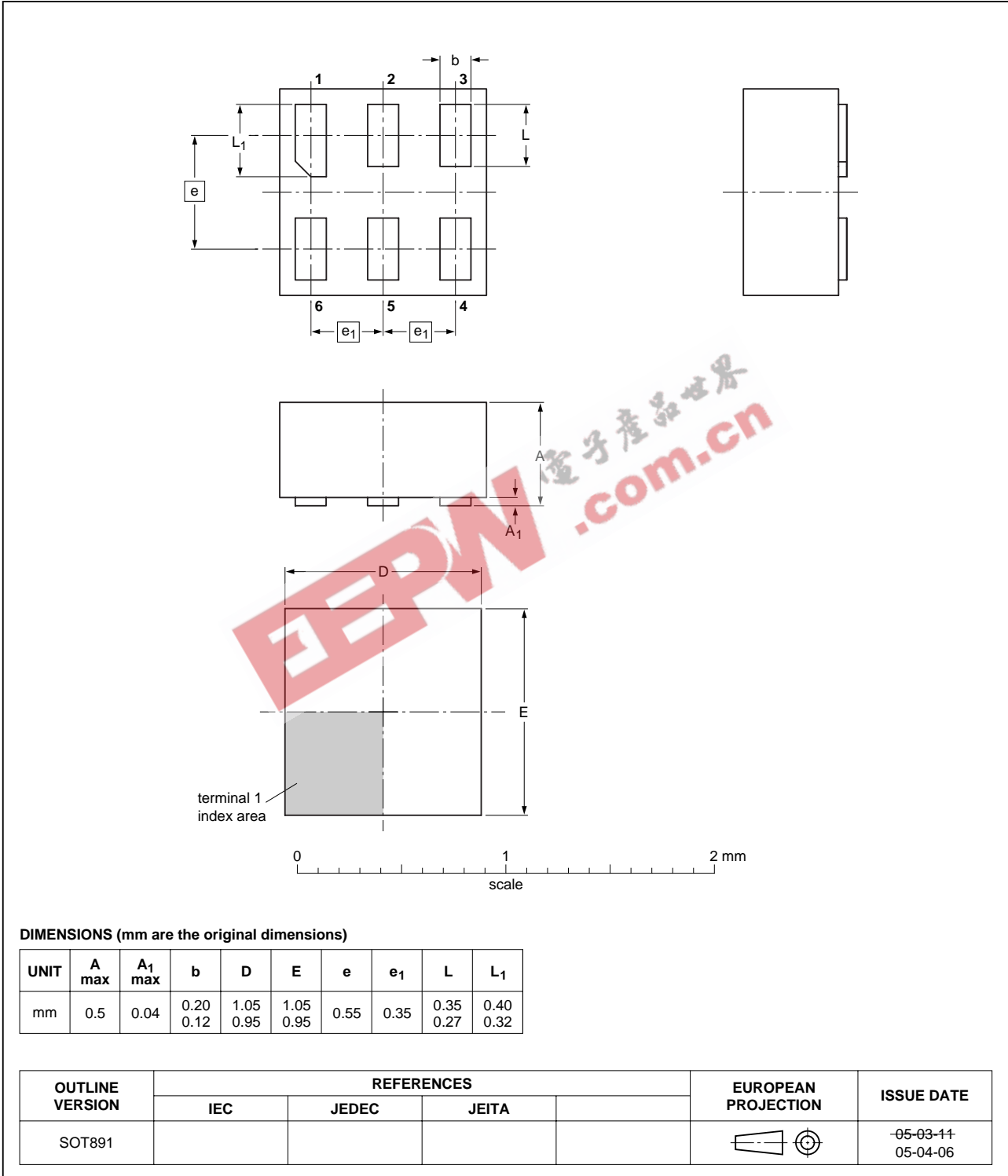


Fig 11. Package outline SOT891 (XSON6)

## 14. Abbreviations

Table 12: Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor Transistor Logic

## 15. Revision history

Table 13: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
74AUP1G86_1	<td>	Product data sheet	-	-	-

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I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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## 21. Contents

1	General description .....	1
2	Features .....	1
3	Ordering information .....	2
4	Marking .....	2
5	Functional diagram .....	2
6	Pinning information .....	3
6.1	Pinning .....	3
6.2	Pin description .....	3
7	Functional description .....	3
8	Limiting values .....	4
9	Recommended operating conditions .....	4
10	Static characteristics .....	5
11	Dynamic characteristics .....	8
12	Waveforms .....	10
13	Package outline .....	12
14	Abbreviations .....	15
15	Revision history .....	15
16	Data sheet status .....	16
17	Definitions .....	16
18	Disclaimers .....	16
19	Trademarks .....	16
20	Contact information .....	16

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Date of release: 16 May 2006  
Document number: 74AUP1G86\_2

Published in The Netherlands